

MITSUBISHI ELECTRIC CORP.

SPEC. SHEET	Drawn	M. Koyama	A	B	C					
	Approved	K. Kurumada Dec '85								
Type No.	2SC2312									
Application	RF POWER AMPLIFICATION									
Structure	NPN Silicon Epitaxial Planar Type Transistor									
Outline	Fig. 1									
Absolute max. ratings	V _{CB0}	V _{EB0}	V _{CE0}	I _c	I _e	P _c	P _e	T _j	T _{stg}	T _c
Condition			R _{BE} = ∞			T _c = 25°C	T _a = 25°C			25°C ±3°C
Limits	60 V	5 V	20 V	6 A	— A	25 W	— W	+150°C	-55°C +150°C	
Parameter	Symbol	Conditions	Values			Unit	AQL (%)			
			MIN.	TYP.	MAX.					
Emitter to Base Breakdown Voltage	V _{(BR)EBO}	I _E = 5mA I _C = 0	5			V	0.65			
Collector to Base Breakdown Voltage	V _{(BR)CBO}	I _C = 1mA I _E = 0	60			V	0.65			
Collector to Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 10mA R _{BE} = ∞	20			V	0.65			
Collector Cutoff Current	I _{CBO}	V _{CB} = 30V I _E = 0			500	μA	0.65			
Emitter Cutoff Current	I _{EBO}	V _{EB} = 4V I _C = 0			100	μA	0.65			
DC Forward Current Transfer Ratio	H _{FE} ^{*1, 2}	V _{CE} = 10V I _C = 1A	35		180	—	0.65			
Output Power	P _o	V _{CC} =12V, f=27MHz, P _{in} =1.5W	17	18.5		W	0.65			
Collector Efficiency	η _c	Same as above	60	70		%	0.65			
Load VSWR ^{*3}										

Notes: 1. Pulsed test.
 2. See Table 1. hFE Classification.
 3. Open and short test at the output terminal of the test circuit when operated at V_{CC}=16V, f=27MHz, P_o=20W.

Table 1. hFE Classification

Item	hFE	Ident.
B	35 - 70	BB
C	55 - 110	CC
D	90 - 180	DD

RF POWER TRANSISTOR -	2SC2312 - E22 - A	SPEC. SHEET
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Fig.1 Outline Drawing.

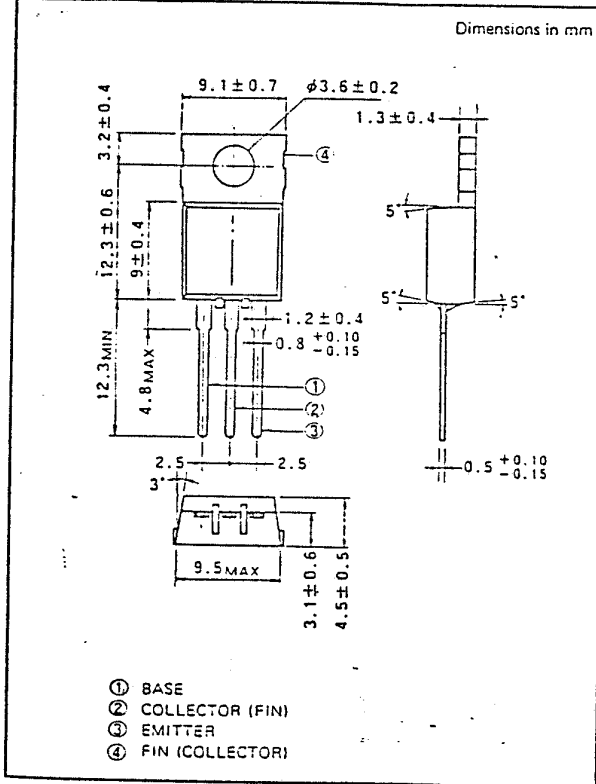


Fig.2 Test Circuit.

